

<b>PTO/SB/08A</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	Not Yet Assigned <i>10/05/02</i>
				Filing Date	Herewith <i>07/08/2003</i>
				First Named Inventor	Henry W. White
Sheet	1	of	3	Attorney Docket No.	UMO 1512.2

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
FH.	1	3,713,822		Kiess	01-30-1973
	2	3,728,784		Schmidt	04-24-1973
	3	3,728,785		Schmidt	04-24-1973
	4	3,801,384		Schmidt	04-02-1974
	5	4,626,322		Switzer	12-02-1986
	6	5,141,564		Chen et al.	08-25-1992
	7	5,274,251		Ota et al.	12-28-1993
	8	5,248,631		Park et al.	09-28-1993
	9	5,574,296		Park et al.	11-12-1996
	10	5,620,557		Manabe et al.	04-15-1997
	11	5,679,965		Schetzina	10-21-1997
FH.	12	5,689,123		Major et al.	11-18-1997
FH.	13	5,846,844		Akasaki et al.	12-08-1998

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T <sup>6</sup>
		Office	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)			

Examiner Signature		Date Considered	<i>4/6/05</i>
--------------------	--	-----------------	---------------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

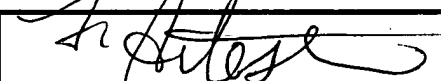
Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

<b>PCT/IB/08A</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	Not Yet Assigned <sup>10/6/15/102</sup>
				Filing Date	Herewith 7/8/2003
				First Named Inventor	Henry W. White
Sheet	2	of	3	Attorney Docket No.	UMO 1512.2

F.H.	14	EPO	EP 0 863 555	A2	Masashi et al.	09-09-1998	
F.H.	15	PCT	WO 00/08691		White et al.	02-17-2000	

### OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.					T <sup>6</sup>
F.H.	16	BAGNALL et al., Optically pumped lasing of ZnO at room temperature, <i>Appl. Phys. Lett.</i> , April 1997, pp. 2230-32, Vol. 70, No. 17					
↑	17	CRACIUN et al., Growth of ZnO thin films on GaAs by pulsed laser deposition, <i>Thin Solid Films</i> , 1995, pp. 1-4					
	18	GUNSHOR et al., Blue-green laser-diode technology moves ahead, <i>Laser Focus World</i> , March 1995, pp. 97-100					
	19	HIRAMATSU et al., Transparent conducting ZnO thin films prepared by XeCl excimer laser ablation, <i>J. Vac. Sci. Technol.</i> , Mar/Apr. 1998, pp. 669-73, Vol. 16, No. 2					
	20	MINEGISHI et al., Growth of p-type Zinc Oxide Films by Chemical Vapor Deposition", <i>J. Appl. Phys.</i> , 1997, pp. 1453-55, Vol. 36, Pt. 2, No. 11A					
	21	JOSEPH et al., p-Type Electrical Conduction in ZnO Thin Films by Ga and N Codoping, <i>Jpn. J. Appl. Phys.</i> , November, 1999, pp. L1205-07, Vol. 38, Part 2, No. 11A, Japanese Journal of Applied Sciences					
	22	MOHAMMAD et al., Reactive Molecular-Beam Epitaxy for Wurzite GaN, <i>MRS Bulletin</i> , Feb. 1997, pp. 22-28					
	23	NAKAMURA, Blue-Green Light Emitting Diodes and Violet Laser Diodes, <i>MRS Bulletin</i> , Feb. 1997, pp. 29-35					
	24	OHTOMO et al., Mg <sub>2</sub> Zn <sub>1-x</sub> as a II-VI widegap semiconductor alloy, <i>Appl. Phys. Lett.</i> , May 1998, pp. 2466-68, Vol. 72, No. 19					
✓	25	PEARTON et al., GaN and Related Materials for Device Applications, <i>MRS Bulletin</i> , Feb. 1997, pp. 17-21					
F.H.	26	PONCE, Defects and Interfaces in GaN Epitaxy, <i>MRS Bulletin</i> , Feb. 1997, pp. 51-57					

Examiner Signature		Date Considered	4/6/05
--------------------	---	-----------------	--------

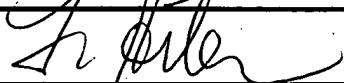
\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

PTO/SB/08A				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	Not Yet Assigned <sup>10/16/15, 10/2</sup>
				Filing Date	Herewith 7/8/2003
				First Named Inventor	Henry W. White
Sheet	3	of	3	Attorney Docket No.	UMO 1512.2

EVH	27	REYNOLDS et al., Similarities In The Bandedge And Deep-Centre Photoluminescence Mechanisms of ZnO and GaN, <i>Solid State Comm.</i> , 1997, pp. 643-46, Vol. 101, No. 9	
↑	28	SHUR et al., GaN/AlGaIn Heterostructure Devices: Photodetectors and Field-Effect Transistors, <i>MRS Bulletin</i> , Feb. 1997, pp. 44-50	
↓	29	ZOLPER et al., Implantation and Dry Etching of Group-III-Nitride Semiconductors, <i>MRS Bulletin</i> , Feb. 1997, pp. 36-43	
↓	30	International Search Report, PCT/US 99/17486	
EVH	31	International Search Report, PCT/US00/41952	

Examiner Signature		Date Considered	4/6/05
--------------------	---	-----------------	--------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.